

Title (en)
METHOD AND COMPOSITION FOR POLISHING BY CMP

Title (de)
ZUSAMMENSETZUNG UND VERFAHREN ZUR CHEMISCH-MECHANISCHEN POLIERUNG

Title (fr)
PROCEDE ET COMPOSITION DE POLISSAGE PAR CMP

Publication
EP 1380048 A1 20040114 (EN)

Application
EP 01916557 A 20010312

Priority
US 0107734 W 20010312

Abstract (en)
[origin: WO02073681A1] A polishing composition for polishing a semiconductor wafer includes a source of chloride ions in solution, which reduces surface roughness of copper interconnects that are recessed in the wafer. High points on the copper interconnects are polished during a polishing operation, while the chloride ions migrate to electric fields concentrated at the high points. The chloride ions at the high points deter replating of copper ions from solution onto the high points. The copper ions replate evenly over the surface on the interconnects, which reduces the surface roughness of the interconnects.

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H01L 21/321; C09G 1/02; C23F 3/06

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CPC (source: EP KR)
C23F 3/00 (2013.01 - EP); **H01L 21/304** (2013.01 - KR); **H01L 21/3212** (2013.01 - EP)

Citation (search report)
See references of WO 02073681A1

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